

**Amendments to the Claims:**

The listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (Currently Amended) A semiconductor pressure sensor, comprising:  
a substrate,  
a diaphragm ~~formed~~ arranged on said substrate, the diaphragm comprising an etch channel; by a sacrificial layer etching method, and  
a silicon oxide film covering said diaphragm and sealing said etch channel,  
~~for sealing an etchant filling hole of a sacrificial layer on said diaphragm; and~~  
~~said semiconductor pressure sensor characterized in that~~ a polysilicon film with a first side covering is provided to cover part or all of said silicon oxide film and a second side exposed to an environment of the pressure sensor.

2. (Currently Amended) A semiconductor pressure sensor according to Claim 1, ~~characterized in that~~ wherein a distance of said covered part is at least 10 microns or less from said etch channel ~~etchant filling hole.~~

3. (Currently Amended) A semiconductor pressure sensor according to Claim 1, ~~characterized in that~~ wherein a thickness of said polysilicon film is 0.1 microns or more.

4. (Currently Amended) A semiconductor pressure sensor according to Claim 1, ~~characterized in that~~ wherein a thickness of said polysilicon film is 0.1 microns or more up to and including 0.4 microns.

5. (Currently Amended) A pressure detector, comprising:

(a) a detector providing an output, the detector including as an integral unit;

a substrate,

a diaphragm ~~formed~~ arranged on said substrate, the diaphragm comprising an etch channel; by a sacrificial layer etching method,

a silicon oxide film covering said diaphragm and sealing said etch channel,  
~~for sealing an etchant filling hole of a sacrificial layer on said diaphragm,~~ and

a polysilicon film with a first side covering part or all of said silicon oxide film and a second side exposed to an environment of the pressure sensor;

(b) a correction circuit for correction of the output of said detector;

(c) a package enclosing said correction circuit and said detector; and

(d) an intake tube provided in said package, the intake tube being used for introducing external pressure to said detector.

6. (Currently Amended) A pressure detector according to Claim 5, ~~characterized in that~~ wherein a distance (h) of said covering part is at least 10 microns or less from said etch channel ~~etchant filling hole~~.

7. (Currently Amended) A pressure detector according to Claim 5, ~~characterized in that~~ wherein a thickness (i) of said polysilicon film is 0.1 microns or more.

8. (Currently Amended) A pressure detector according to Claim 5, ~~characterized in that~~ wherein a thickness (j) of said polysilicon film is 0.1 microns or more up to and including 0.4 microns.

9. (Currently Amended) A pressure detector according to Claim 5 comprising:

(e) a sub-package further comprising said correction circuit and said detector as an integral unit, and having on a surface a pad connected to said correction circuit, and

(f) an output terminal removably connected to an external signal line and being used to send a signal from said correction circuit to the external signal line;

~~said pressure detector further characterized in that~~

(g) wherein said correction circuit and said detector are enclosed by said package after said pad and said output terminal are connected by a metal wire.

10. (Currently Amended) A semiconductor pressure sensor, comprising:  
a substrate;

a diaphragm arranged on the substrate, a gap between the diaphragm and the substrate being formed by sacrificial layer etching using etch channels arranged about a periphery of the diaphragm;

a silicon oxide film arranged over the diaphragm in order to seal the etch ~~etching~~ channels; and

a polysilicon film covering at least a substantial portion of the silicon oxide film.

11. (New) A semiconductor pressure sensor according to claim 10, wherein the polysilicon film has a first side covering at least a substantial portion of the oxide film and a second side exposed to an environment of the pressure sensor.

12. (New) A semiconductor pressure sensor according to claim 11, wherein the pressure sensor is an electrostatic capacity or piezoresistive pressure sensor.